

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

MAY 13 2002

Docket Number (Optional)

BUR920010127US1

Application Number

Not Yet Assigned

Applicant(s)

Abadeer, et al.

Filing Date

Concurrently herewith

Group Art Unit

Not Yet Assigned

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MBS		US 6,180,464 B1	1/30/01	Krivokapic, et al.	—	—	
		US 5,379,321	1/3/95	Girmay	—	—	
		US 5,532,175	7/2/96	Racanelli	—	—	
		US 5,457,336	10/10/95	Fang, et al.	—	—	
		US 6,047,247	4/4/00	Iwanishi, et al	—	—	
		US 5,654,896	8/5/97	Ochi	—	—	
		US 5,696,452	12/9/97	Hemmenway, et al	—	—	
		US 5,900,741	5/4/99	Roohparvar	—	—	
MBS		US 5,587,665	12/24/96	Jiang	—	—	

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

SHINGLETON

DATE CONSIDERED

July 1, 2003

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>		Docket Number (Optional) BUR9200100127651	Application Number Not Yet Assigned
		Applicant(s) Abadeer et al.	
		Filing Date Concurrently Herewith	Group Art Unit Not Yet Assigned
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>			
*EXAMINER INITIAL	S. Ogasawara and N. Shiono, "Generalized Diffusion-Reaction model for the Low-Field Charge-Buildup Instability at the Si-SiO ₂ Interface, "Phys. Rev. B, vol. 51, pp. 4218-4230, 1995.		
MBS	Wagdi W. Abadeer, William R. Tonti, Wilfried H. Hansch, and Udo Schwalke, "Long-Term Temperature Reliability of P+ Polysilicon Gated Devices, "IEEE TRANSACTIONS ON ELECTRON DEVICES, vol. 42, No. 2, pp. 360-362, 1995.		
	Shigeo Ogawa, Masakazu Shimaya, and Noburu Shiono, "Interface-Trap Generation at Ultra-thin SiO ₂ (4-6 nm)-Si Interfaces During Negative-Bias Temperature Aging, "J. Appl. Phys. 77 (3), 1 February 1995, pp. 1137-1148, 1995.		
	G. LaRosa, F. Guarin, S. Rauch, A. Acovic, J. Lukaitis, and E. Crabbe, "NBTI-Channel Hot Carrier Effects in PMOSFETS in Advanced CMOS Technologies, "Proceedings of the 35th Annual IEEE International Reliability Physics Symposium (IRPS), pp. 282-286, 1997.		
	Toveji Yamamoto, Ken ichi Uwasawa, and Tohru Mogami, "Bias Temperature Instability in Scaled P+ Polysilicon Gate p-MOSFET's, "IEEE Transactions on Electron Devices, vol. 46, No. 5, pp. 921-926, 1999.		
	Mariko Makabe, Taishi Kubota, and Tomohisa Kitano, "Bias-Temperature Degradation of pMOSFETs: Mechanism and Suppression, "Proceedings of the 38th Annual IEEE International Physics Symposium (IRPS), pp. 205-209, 2000.		
MBS	C.H. Liu, Y.F. Chen, S.K. Fan, M.T. Lee, M.H. Lin, C.H. Chou, W.C. Chang, S.C. Huang, Y.J. Cjang, and K.Y. Fu, "Negative Bias Temperature Instability (NBTI) in Deep Sub-Micron P+ Gate pMOSFETs, "Proceedings of the International Integrated Reliability Workshop, pp 98-100, 2000.		
EXAMINER SHINGLETON	DATE CONSIDERED July 1, 2003		
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